

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SD2012

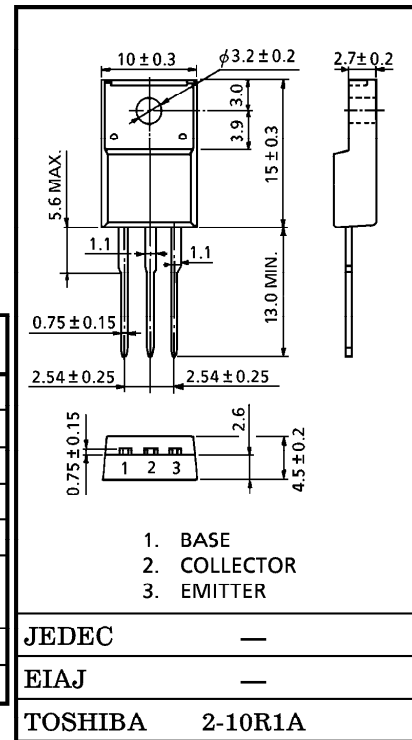
AUDIO FREQUENCY POWER AMPLIFIER APPLICATIONS

Unit in mm

- High DC Current Gain : $h_{FE(1)}=100$ (Min.)
- Low Saturation Voltage
: $V_{CE(sat)}=1.0V$ (Max.)
- High Power Dissipation : $P_C=25W$ ($T_c=25^\circ C$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CB0}	60	V
Collector-Emitter Voltage		V_{CEO}	60	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current		I_C	3	A
Base Current		I_B	0.5	A
Collector Power Dissipation	$T_a=25^\circ C$	P_C	2.0	W
	$T_c=25^\circ C$		25	
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{stg}	-55~150	$^\circ C$



Weight : 1.7g (Typ.)

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=60V, I_E=0$	—	—	100	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=7V, I_C=0$	—	—	100	μA
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C=50mA, I_E=0$	60	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=0.5A$	100	—	320	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=2A$	20	—	—	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=0.2A$	—	0.4	1.0	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=0.5A$	—	0.75	1.0	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=0.5A$	—	3	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	—	35	—	pF

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